



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-89 Plastic-Encapsulate Transistors

BCX52 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 0.5 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -1 A

Collector-base voltage

$V_{(BR)CBO}$: -60 V

Operating and storage junction temperature range

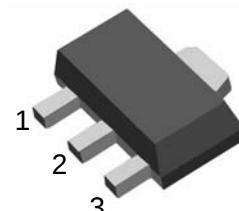
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-89

1. BASE

2. COLLECTOR

3. EMITTER



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-60		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB}=-30V, I_E=0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-2V, I_C=-150mA$	63	250	
	$h_{FE(2)}$	$V_{CE}=-2V, I_C=-5mA$	63	160	
	$h_{FE(3)}$	$V_{CE}=-2V, I_C=-500mA$	100	250	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-50mA$		-0.5	V
Base-emitter voltage	$V_{BE(ON)}$	$I_C=-500mA, V_{CE}=-2V$		-1	V
Transition frequency	f_T	$V_{CE}=-5V, I_C=-10mA$ $f=100MHz$	50		MHz

DEVICE MARKING	BCX52=AE BCX52-10=AG BCX52-16=AM
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